		Application No.	Applicant(s)	
	Notice of Allowability	10/607,033		
		Examiner	BONART ET AL.	
-		Thao P Le	2818	
Th MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS Of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.				
	This communication is responsive to <u>6/26/03</u> .	and MPEP 1308.		
2. 🖂	The allowed claim(s) is/are <u>1-13</u> .			
3. 🖂	3. A classified on <u>26 June 2003</u> are accepted by the Examiner.			
4. 🖾	4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).			
-	Thome of the:		(1)	
	Certified copies of the priority documents have	been received.		
	2. U Certified copies of the priority documents have been received in Application No.			
	3. U Copies of the certified copies of the priority documents have been received in this national stage application from the			
:	international Bureau (PCT Rule 17.2(a))		stage application from the	
5. 🗆	* Certified copies not received:			
reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78. (a) The translation of the foreign language provisional application has been received.				
O. L. Acknowledgment is made of a claim for domestic priority under 25 H C.O. SS 400				
' l'	The state of the s	Data Offeet: 37 CFR 1.76.		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.				
INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient				
8. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached.				
Interest of 2) to Paper No				
(b) including changes required by the proposed drawing correction filed, which has been approved by the Examiner.				
(6)	(c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
ldentifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the margin according to 37 CFR 1.121(d).				
9. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.				
Attachn	nent(s)			
1⊠ Not	ce of References Cited (PTO-892)	5 Notice of Inform	d Bata (A source of the sourc	
 2☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3☑ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No. dated 6/26/03 4☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 		6 Interview Summ	al Patent Application (PTO-152)	
		7☐ Examiner's Ame	ary (PTO-413), Paper No	
		8⊠ Examiner's Statement of Reasons for Allowance		
		9☐ Other	THERE OF REASONS FOR Allowance	
			·V·	

DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

2. The information disclosure statement (IDS) submitted on 6/26/03 was filed on the same mailing date of the application. The submission is in compliance with the provisions of 37 CFR 1.97. Accordingly, the information disclosure statement is being considered by the examiner.

Allowable Subject Matter

- 3. Claims 1-13 are allowed.
- 4. Claims 1-13 are considered allowable since none of prior art teach or suggest claimed limitations having a method of forming a buried strap contact between a transistor and a trench capacitor in a memory cell to provide an efficient and effective manufacturing method that allows a miniaturization of the memory cell without negatively influencing the performance of the memory cell. The method including the steps of forming a trench capacitor in a substrate whereas the trench having lower region filled with a first doped filler material having a first width and comprising an open, unfilled region adjacent to it, filling the unfilled region, generating gate paths on the

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substrate, etching, for generating a buried strap contact, a contact trench having a second width at least down to a depth of the floor formed by the first doped filler material, the gate paths forming at least part of a mask utilized for etching the contact trench.

Conclusion

- 5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao P Le whose telephone number is 571-272-1785. The examiner can normally be reached on M-T (8:00-6:30).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-1956.

Supervisory Patent Examiner Technology Center 2800

Thao P. Le